

Unraveling Structure-Performance Relationships: Tailored d-band Centers in monolayer MSi_2N_4 and MoSi_2Z_4 by Atomic Substitution

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Table S1 The lattice constants (a), alterations in bond lengths (d_1-d_4), angles ($\theta_1-\theta_4$) and band gaps of monolayer MSi_2N_4 and MoSi_2Z_4

	a(Å)	d_1 (Å)	d_2 (Å)	d_3 (Å)	d_4 (Å)	θ_1 (°)	θ_2 (°)	θ_3 (°)	θ_4 (°)	E_g (eV)
MoSi_2N_4	2.91	6.99	1.75	1.75	2.09	112.09	106.71	88.22	73.01	1.70
CrSi_2N_4	2.84	6.86	1.72	1.75	2.00	110.74	108.17	90.36	70.02	0.51
WSi_2N_4	2.90	7.01	1.75	1.74	2.10	112.26	106.60	87.84	73.60	2.13
TaSi_2N_4	2.96	7.00	1.78	1.75	2.12	112.70	106.00	88.29	72.94	/
TiSi_2N_4	2.92	6.90	1.76	1.75	2.06	111.86	106.96	90.1	70.44	1.63
ZrSi_2N_4	3.03	7.04	1.81	1.75	2.18	113.27	105.34	88.26	72.97	1.57
HfSi_2N_4	3.02	6.99	1.80	1.75	2.18	112.95	105.65	88.80	72.12	1.63
MoSi_2P_4	3.46	9.36	2.25	2.23	2.45	100.73	117.22	89.75	70.88	0.69
MoSi_2As_4	3.61	9.90	2.36	2.34	2.56	99.43	118.25	89.56	71.15	0.60

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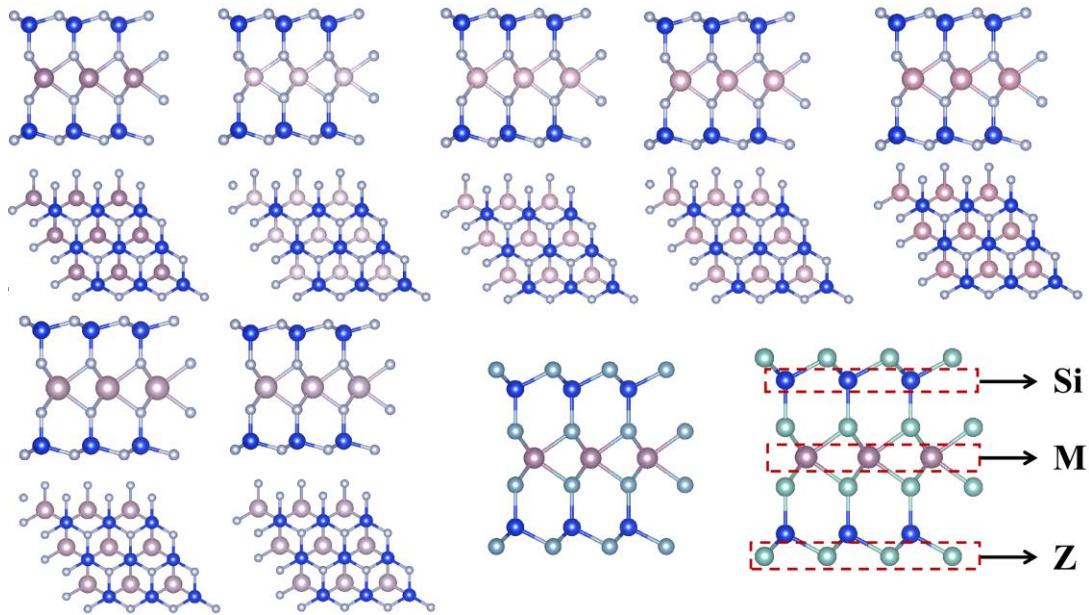


Fig. S1 Side view and top view of monolayer MSi_2N_4 ($\text{M} = \text{Mo, Cr, W, Ta, Ti, Zr and Hf}$) and MoSi_2Z_4 ($\text{Z} = \text{P and As}$)

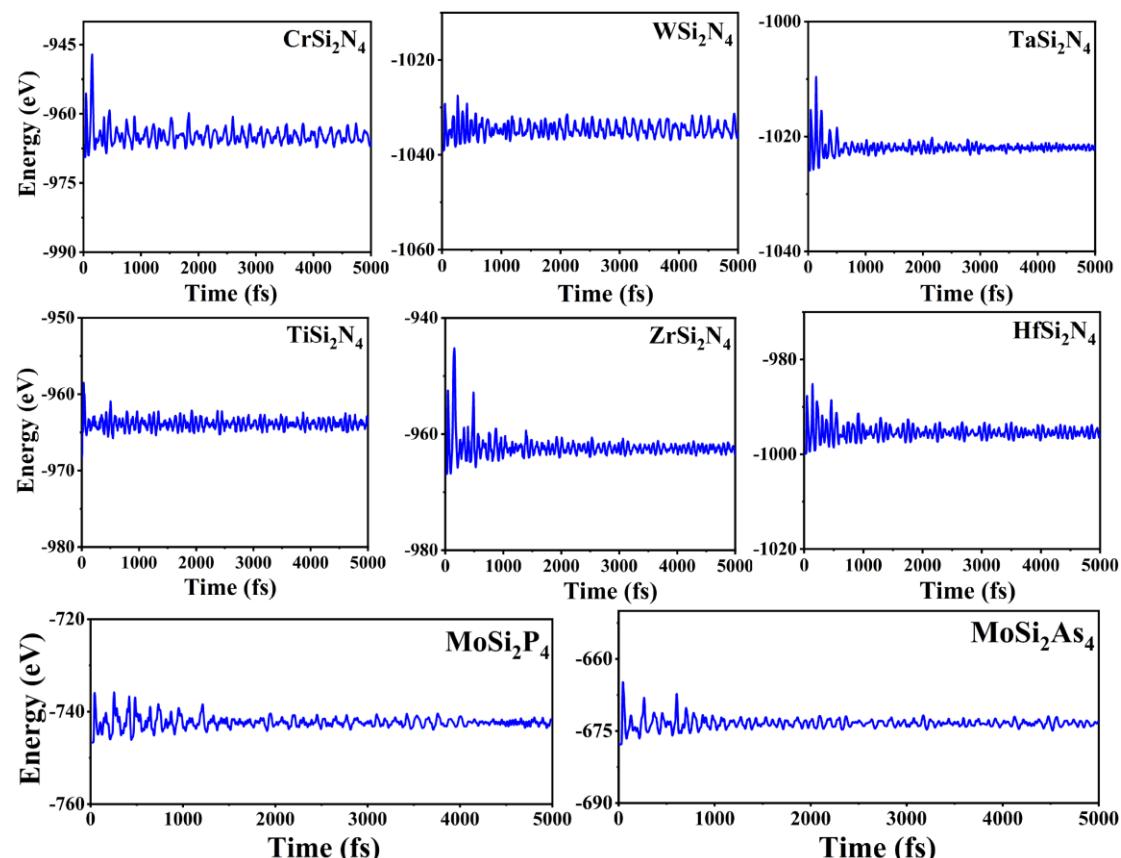


Fig. S2 The free energy and temperature over 5 ps during AIMD at 300 K of monolayer MSi_2N_4 and MoSi_2Z_4

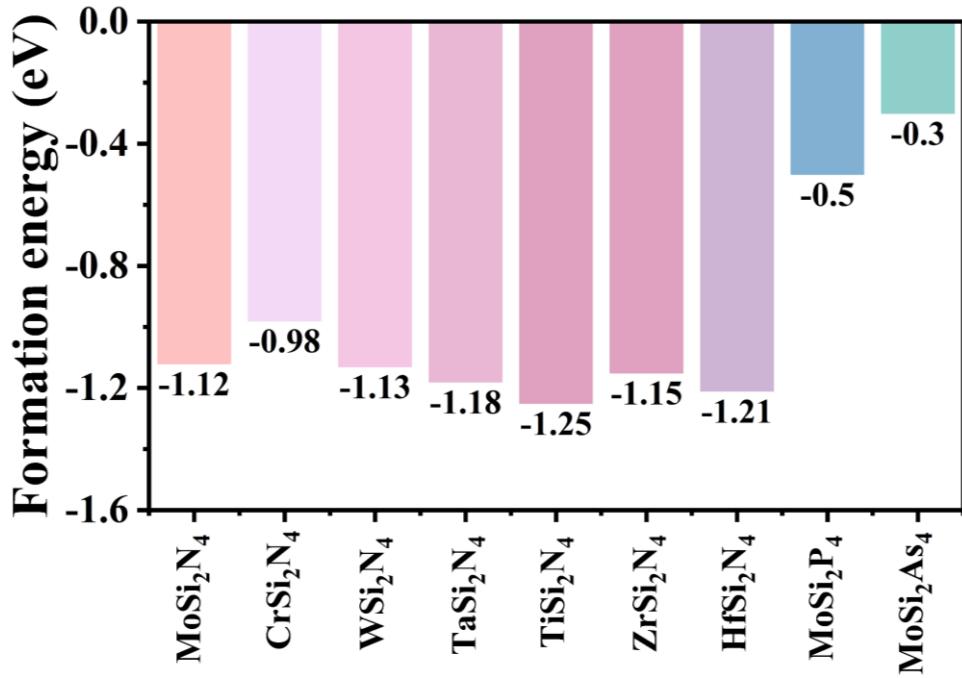


Fig. S3 The formation energy of monolayer MSi₂N₄ and MoSi₂Z₄

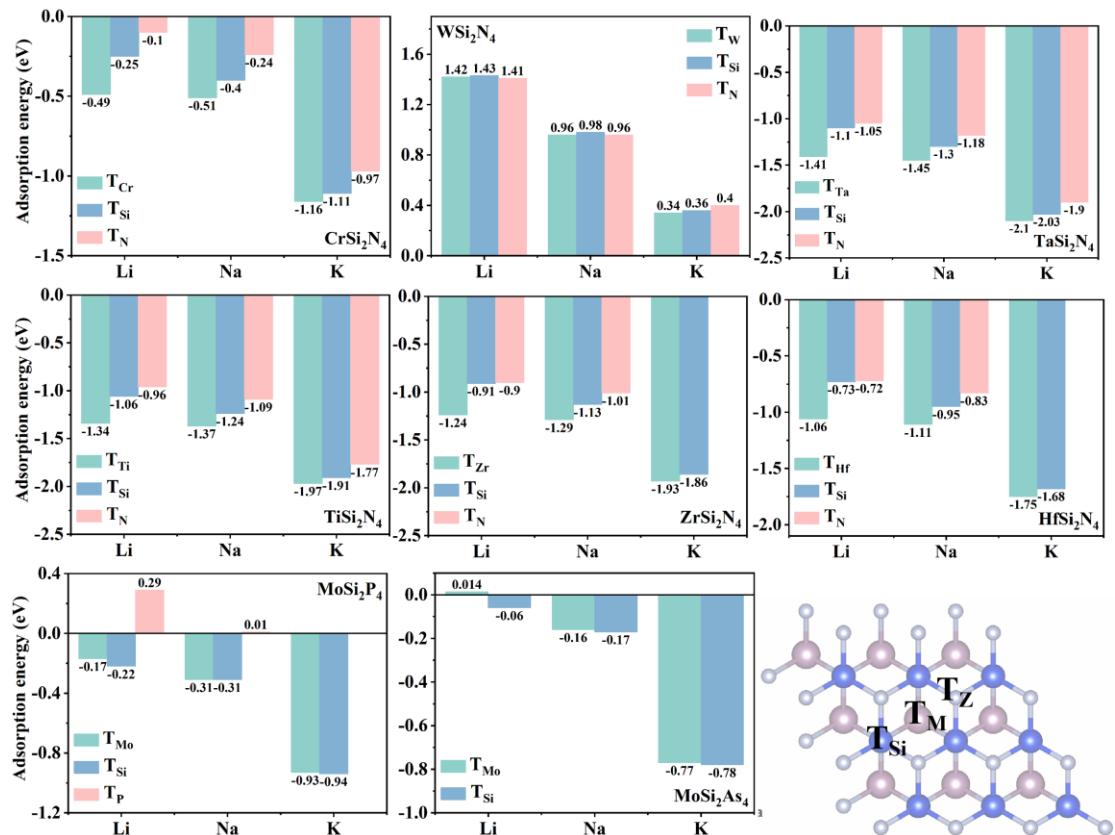


Fig. S4 The adsorption energy of stable adsorption site for alkali metal atoms of monolayer MSi₂N₄ and MoSi₂Z₄

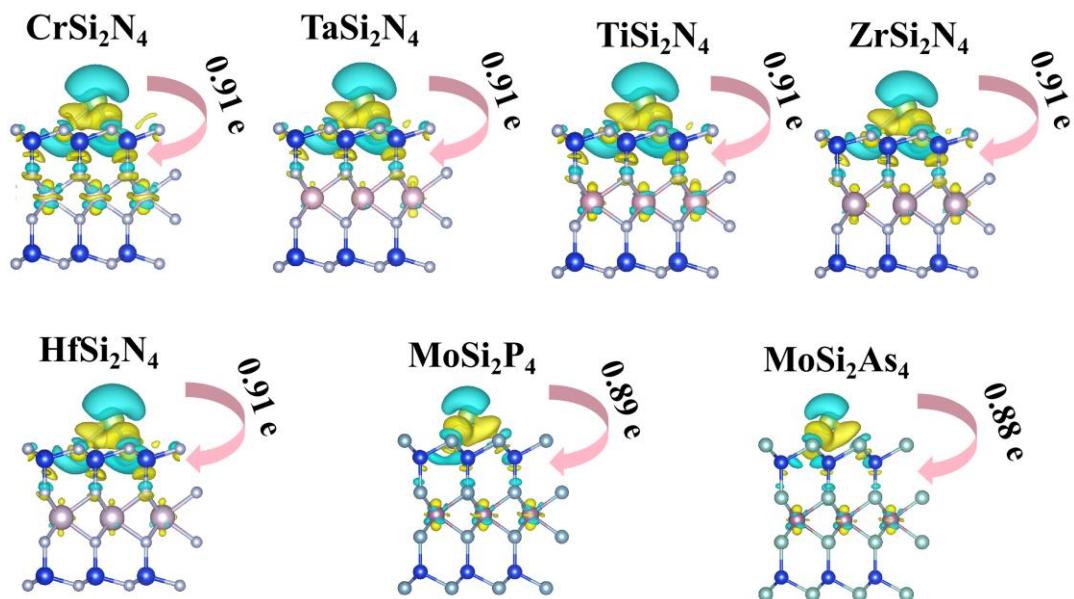


Fig.S5 The charge density difference at the most stable positions of Li adsorption on monolayer MSi_2N_4 and MoSi_2Z_4

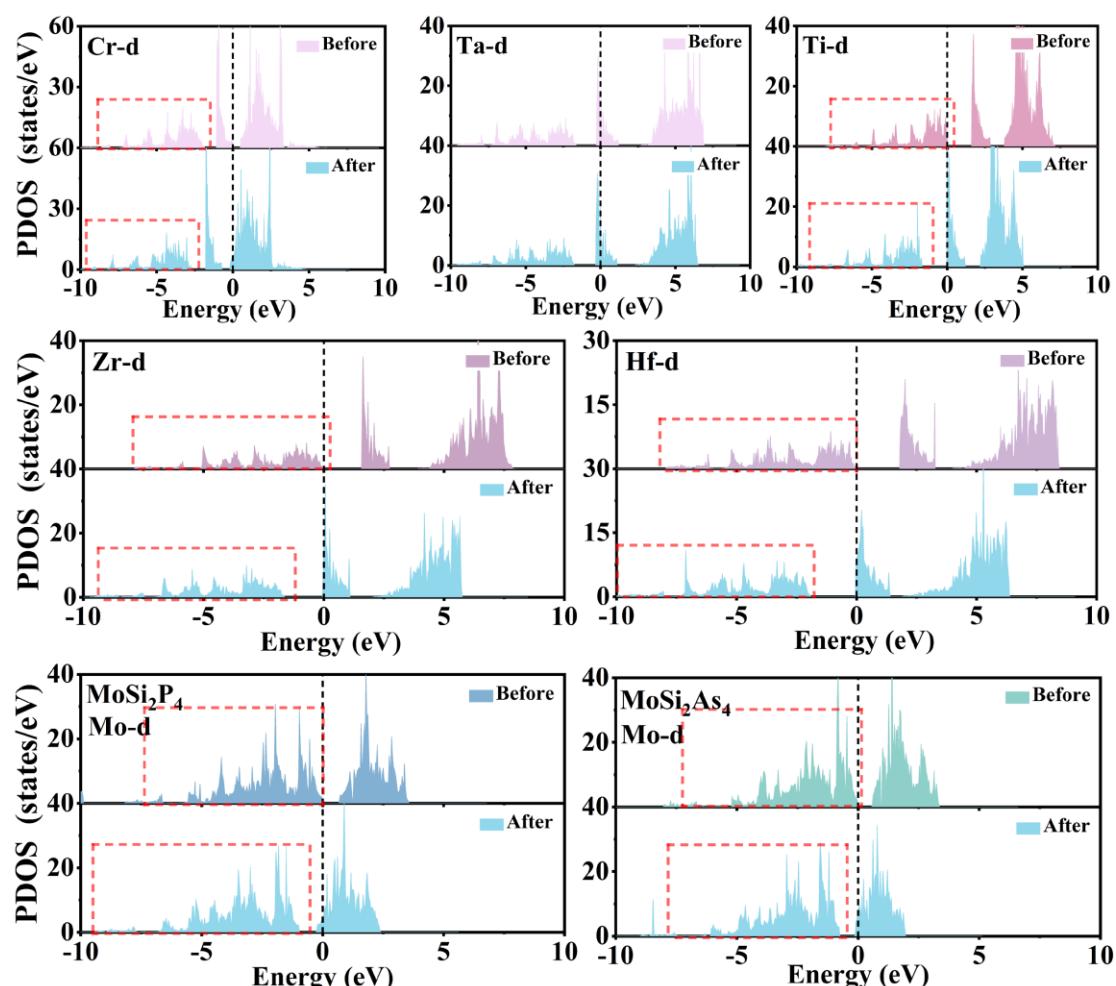


Fig.S6 The PDOS of TMs before and after Li adsorption

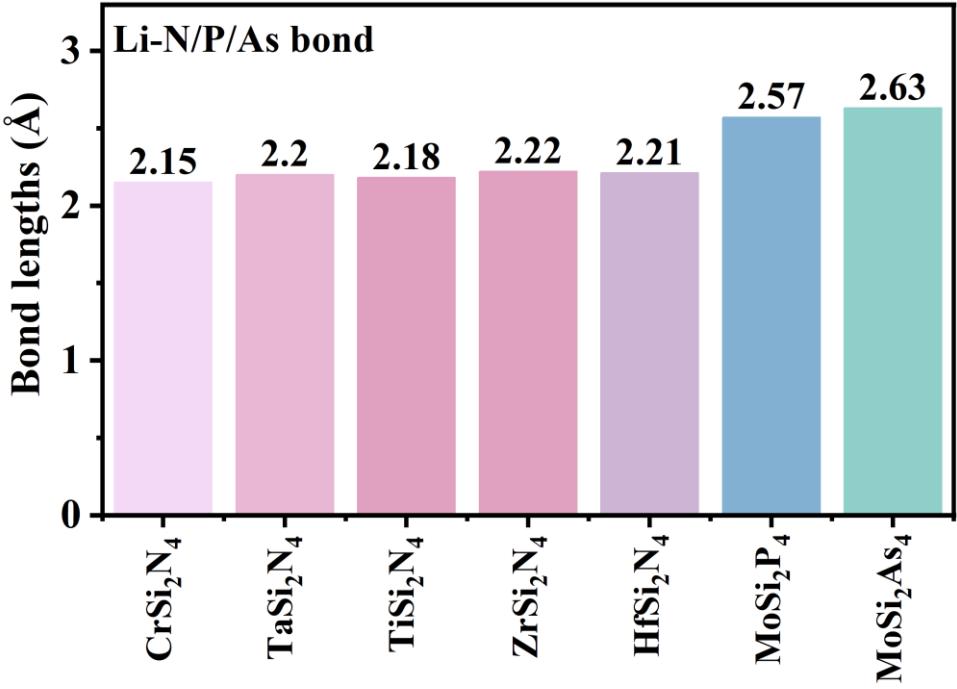


Fig. S7 The bond lengths at the most stable positions of Li adsorption on monolayer MSi_2N_4 and MoSi_2Z_4

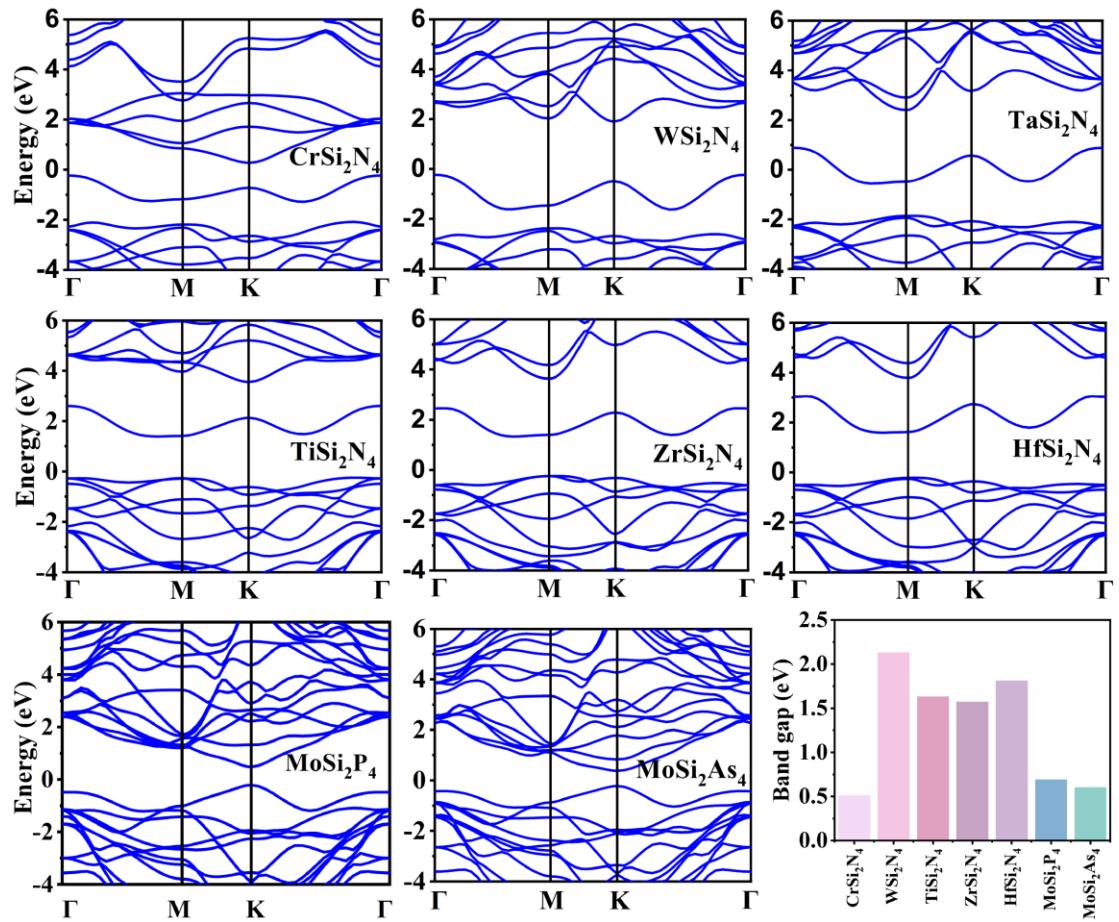


Fig. S8 The band structures of monolayer MSi_2N_4 and MoSi_2Z_4

Table S2 Elastic Properties of MSi_2N_4 and MoSi_2Z_4 (Elastic Constants C_{ij} , Shear Modulus G^{2D} , Young's Modulus Y in N/m, and Poisson's Ratio ν)

	C_{11}	C_{12}	C_{22}	$C_{66}=G^{2D}$	$Y_{[x]}$	$Y_{[y]}$	$\nu_{[x]}$	$\nu_{[y]}$
CrSi_2N_4	523.71	154.37	523.71	184.67	478.21	478.21	0.30	0.30
WSi_2N_4	574.64	158.07	574.64	208.29	531.16	531.16	0.28	0.28
TaSi_2N_4	518.85	166.10	518.85	176.37	465.67	465.67	0.32	0.32
TiSi_2N_4	498.16	153.31	498.16	172.43	450.98	450.98	0.31	0.31
ZrSi_2N_4	437.89	138.86	437.89	149.52	393.85	393.85	0.32	0.32
HfSi_2N_4	459.25	156.23	459.25	151.51	406.11	406.11	0.34	0.34
MoSi_2P_4	218.90	55.57	218.90	81.67	204.80	204.80	0.25	0.25
MoSi_2As_4	181.46	52.83	181.46	64.32	166.08	166.08	0.29	0.29

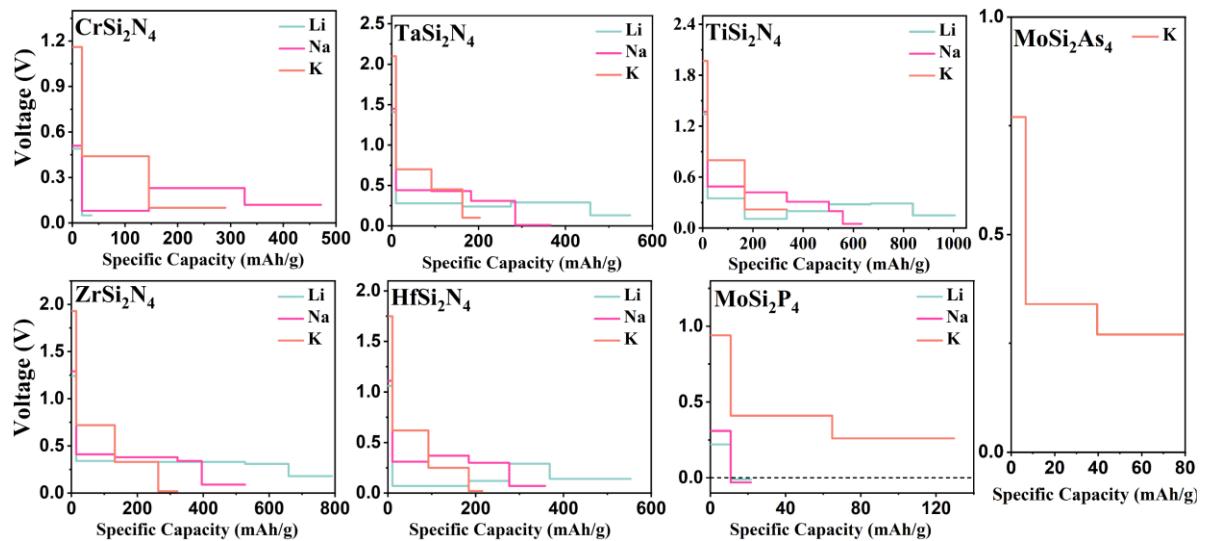


Fig. S9 The voltage profiles as a function of specific capacity of monolayer MSi_2N_4 and MoSi_2Z_4